International

FEATURES

- Single input voltage range from 5V to 21V
- Wide input voltage range from 1.0V to 21V with external V_{CC} bias voltage
- Integrated MOSFET drivers, Control FET, Synchronous FET with Schottky diode, bootstrap diode and the internal LDO
- Enable input with voltage monitoring capability
- Logic Level Tri-state PWM input
- Thermally compensated Over Current Indicator
- Open-drain over temperature and over current fault indication
- Under-voltage Lockout of VCC/LDO_Out
- Operating temp: -40°C < T_i < 125°C
- Package size: 5mm x 6mm PQFN
- RoHS6 Compliant, lead-free and halogen-free

DESCRIPTION

The IR3742 integrated PowIRstage[®] is a synchronous buck gate driver IC with co-packed control and synchronous MOSFETs and Schottky diode. It is optimized internally for PCB layout, heat transfer and driver/MOSFET timing. Custom designed gate driver and MOSFET combination enables higher efficiency at lower output voltages required by cutting edge ASIC, FPGA and advanced controller.

Up to 1.5MHz switching frequency enables high performance transient response, allowing miniaturization of output inductors, as well as input and output capacitors while maintaining industry leading efficiency. The IR3742's superior efficiency enables smallest size and lower solution cost.

The IR3742 includes an over current indicator and over temperature indicator in the event of a fault condition.

APPLICATIONS

- Computing Applications
- Set Top Box Applications
- Storage Applications
- Data Center Applications
- Distributed Point of Load Power Architectures

ORDERING INFORMATION

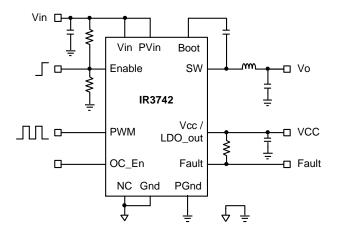
Base Part Number	Package Type	Standar	d Pack	Orderable Part Number	
Dase Fait Number	Гаскаде Туре	Form	Quantity	Orderable Part Number	
IR3742	PQFN 5 mm x 6 mm	Tape and Reel	4000	IR3742MTRPBF	
		PBF —	Lead Free Tape and Reel		

- M

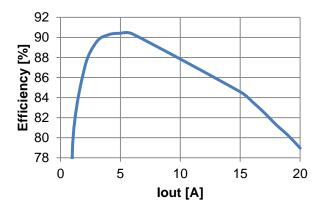


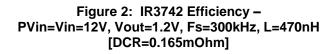
IR3742

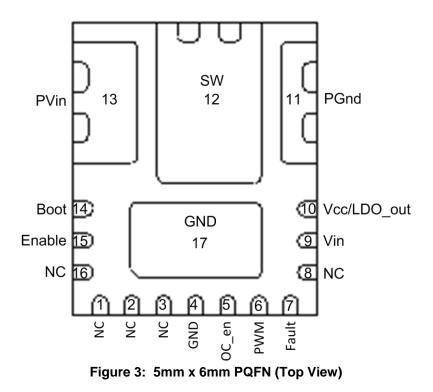
BASIC APPLICATION











PINOUT DIAGRAM



BLOCK DIAGRAM

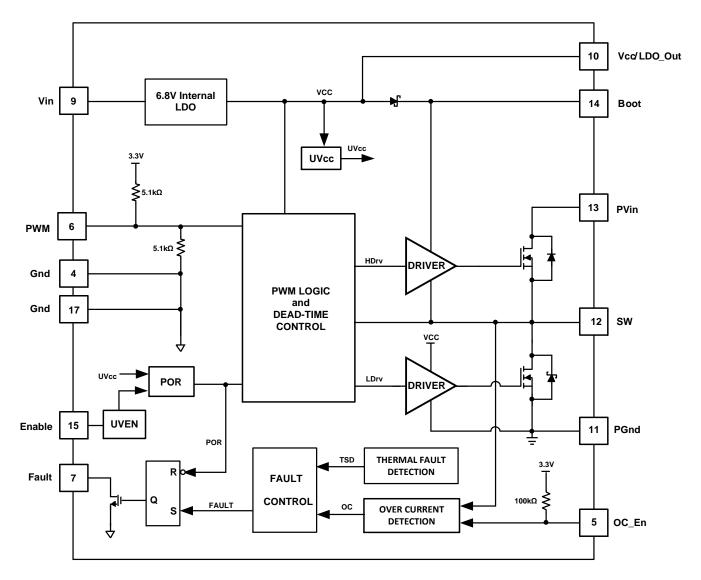


Figure 4: Simplified Block Diagram

PIN DESCRIPTIONS

PIN #	PIN NAME	PIN DESCRIPTION
1, 2, 3, 8, 16	NC	Must be connected to signal ground on the PCB layout.
4, 17	Gnd	Signal ground for internal reference and control circuitry.
5	OC_En	Over current detection enable pin. Floating this pin enables the over current detection. Shorting this pin to GND disables the over current detection.
6	PWM	Logic level tri-state PWM input. "High" turns the control MOSFET on, and "Low" turns the synchronous MOSFET on. "Tri-state" turns both MOSFETs off.
7	Fault	Open-drain fault indication. Connect a pull-up resistor from this pin to Vcc. Fault pin stays high when VCC/LDO_Out or Enable voltage is below their thresholds. In normal operation, Fault pin stays high. When over temperature or over current occurs, Fault pin is latched low. Recycle Vcc or Enable to reset.
9	Vin	Input for internal LDO. A 1.0μ F capacitor should be connected between this pin and PGnd. If an external supply is connected to Vcc/LDO_out pin, this pin should be shorted to Vcc/LDO_out pin.
10	Vcc/LDO_Out	Output of the internal LDO and optional input of an external biased supply voltage. A minimum 2.2µF ceramic capacitor is recommended between this pin and PGnd.
11	PGnd	Power Ground. This pin serves as a separated ground for the MOSFET drivers and should be connected to the system's power ground plane.
12	SW	Switch node. Connect this pin to the output inductor.
13	PV _{in}	Input voltage for power stage.
14	Boot	Supply voltage for high side driver, a 100nF capacitor should be connected between this pin and SW pin.
15	Enable	Enable pin to turn on and off the device. Input voltage monitoring (input UVLO) can also be implemented by connecting this pin to PVin pin through a resistor divider.

ABSOLUTE MAXIMUM RATINGS

Stresses beyond these listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied.

PVin, Vin to PGnd (Note 4)	-0.3V to 25V
Vcc/LDO_Out to PGnd (Note 4)	-0.3V to 8V (Note 1)
Boot to PGnd (Note 4)	-0.3V to 33V
SW to PGnd (Note 4)	-0.3V to 25V (DC), -V _{CC} for 20ns (AC)
Boot to SW	-0.3V to V _{CC} + 0.3V (Note 2)
Fault to Gnd (Note 4)	-0.3V to V_{CC} + 0.3V (Note 2)
PWM, to Gnd	-0.3V to 5V
Enable, OC_En to Gnd (Note 4)	-0.3V to +3.9V
PGnd to Gnd	-0.3V to +0.3V
THERMAL INFORMATION	
Junction to Ambient Thermal Resistance Θ_{jA}	30 °C/W (Note 3)
Junction to PCB Thermal Resistance Θ_{j-PCB}	2 °C/W
Storage Temperature Range	-55°C to 150°C
Junction Temperature Range	-40°C to 150°C

Note 1: Vcc must not exceed 7.5V for Junction Temperature between -10°C and -40°C.

Note 2: Must not exceed 8V.

Note 3: Based on a 4-layer PCB board (2.23"x2") using 2 oz. copper on each layer.

Note 4: PGnd pin and Gnd pin are connected together.

ELECTRICAL SPECIFICATIONS

RECOMMENDED OPERATING CONDITIONS

	SYMBOL	MIN	MAX	UNITS
Input Voltage Range with External Vcc Note 5, Note 7	PV _{in}	1.0	21	
Input Voltage Range with Internal LDO Note 6, Note 7	V _{in} , PV _{in}	5.5	21	V
Supply Voltage Range (Note 6)	V _{CC}	4.5	7.5	
Supply Voltage Range (Note 6)	Boot to SW	4.5	7.5	
Output Current Range	I ₀	0	20	А
Switching Frequency	Fs	300	1500	kHz
Operating Junction Temperature	TJ	-40	125	°C

Note 5: V_{in} is connected to V_{cc} to bypass the internal LDO.

Note 6: V_{in} is connected to PV_{in}. For single-rail applications with PV_{in}=V_{in}<7.4V, the internal LDO may operate in dropout mode. Please refer to the application information of the Internal LDO and the Over Current Protection.

Note 7: Maximum SW node voltage should not exceed 25V.

ELECTRICAL CHARACTERISTICS

Unless otherwise specified, these specifications apply over, $7.4V < V_{in} = PV_{in} < 21V$, 0°C < T_J < 125°C. Typical values are specified at $T_a = 25^{\circ}C$.

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	МАХ	UNITS	
Power Stage		•		8			
Power Losses	P _{LOSS}	$\begin{array}{l} PV_{in} = V_{in} = 12V, \ V_o = 1.2V, \\ I_o = 20A, \ F_s = 600 kHz, \ L = \\ 0.3 uH, \ Note \ 8 \end{array}$		4.98		W	
Top Switch R _{DS(ON)}	R _{DS(on)-T}	$\label{eq:boost} \begin{array}{l} V_{BOOT} - Vsw = 6.8V, \ I_o = 20A, \\ T_j = 25^{\circ}C \end{array}$		8	10.4	mΩ	
Bottom Switch R _{DS(ON)}	R _{DS(on)-B}	$\label{eq:Vcc} \begin{array}{l} V_{cc}=6.8V,\ I_{o}=20A,\\ T_{j}=25^{\circ}C \end{array}$					
Bootstrap Diode Forward Voltage	V _{FWD}	I(Boot) = 15mA	200	370	550	mV	
SW Leakage Current	I _{SW}	$V_{SW} = 0V$, Enable = $0V$			1	μA	
Dead Band Time	T _D	Note 8		10		ns	
PWM Comparator				•	•		
PWM Input High Threshold	V _{PWM} -HIGH	PWM Tri-State to High	2.5			V	
PWM Input Low Threshold	V _{PWM-LOW}	PWM Tri-State to Low			0.8	V	
PWM Tri-State Float Voltage	V _{PWM-TRI}	PWM Floating	1.35	1.65	1.8	V	
Hysteresis	$V_{\text{PWM-HYS}}$	Active to Tri-state or Tri-state to Active, Note 8	0.1	0.2	0.3	V	

ELECTRICAL CHARACTERISTICS (CONTINUED)

Unless otherwise specified, these specifications apply over, 7.4V < $V_{in} = PV_{in} < 21V$, 0°C < $T_J < 125$ °C. Typical values are specified at $T_a = 25$ °C.

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	МАХ	UNITS
Tri-State Propagation Delay	т	PWM Tri-state to low transition of SW node, Note 8		19.8		ns
The State Propagation Delay	T _{PWM-DELAY}	PWM Tri-state to high transition of SW node, Note 8		36.4		ns
PWM Sink Impedance	R _{PWM-SINK}	PWM = 3.3V	3.57	4.8	6.63	kΩ
PWM Source Impedance	R _{PWM-SOURCE}	PWM = GND	3.57	4.8	6.63	kΩ
Internal Pull Up Voltage	V _{PWM-PULLUP}	Vcc > UVLO		3.3		V
Minimum Pulse Width	T _{PWM-MIN}	Note 8		41	58	ns
		Supply Current				
Vin Supply Current (standby)	I _{in(Standby)}	EN = Low, No Switching			125	μA
Vin Supply Current (dynamic)	I _{in(Dyn)}	$ \begin{array}{l} EN=High, \ F_{s}=600 kHz, \\ V_{in}=PV_{in}=21 V \end{array} $		20	23	mA
		V _{cc} /LDO_Out				
Output Voltage	V _{cc}	$\label{eq:Vin(min)} \begin{array}{l} V_{in(min)} = 7.4 V, \ I_o = 0\text{-}50 mA, \\ Cload = 2.2 uF; \ EN = High \end{array}$	6.5	6.8	7.0	V
LDO Dropout Voltage	V _{cc_drop}	V _{in} =6.5V,I₀=50mA, Cload=2.2uF			0.88	V
Short Circuit Current	I _{short}	EN = High		70		mA
		Under-Voltage Lockout				
Vcc-Start Threshold	V _{CC} UVLO Start	V_{cc} rising trip Level	3.9	4.15	4.4	V
V_{cc} -Stop Threshold	V _{CC} UVLO Stop	Vcc falling trip Level	3.5	3.86	4.1	V
Enable-Start-Threshold	Enable UVLO Start	ramping up	1.13	1.19	1.27	V
Enable-Stop-Threshold	Enable UVLO Stop	ramping down	0.85	0.93	1.1	V
Enable Leakage Current	I _{EN_LK}	Enable = 3.3V			1	μA

ELECTRICAL CHARACTERISTICS (CONTINUED)

Unless otherwise specified, these specifications apply over, 7.4V < $V_{in} = PV_{in} < 21V$, 0°C < $T_J < 125$ °C. Typical values are specified at $T_a = 25$ °C.

	Fault						
Over Current Limit	I _{LIMIT}	$T_j = 25^{\circ}C$	29	35	41	А	
Over Temperature Threshold	T _{TSD}	Note 8		145		°C	
Fault Voltage Low	V _{FAULT}	I _{FAULT} = -5mA			0.5	V	
OC_EN Fault Disable Threshold	OCDISABLE	Note 8			0.8	V	

Note 8: Guaranteed by design, but not tested in production.

I R

TYPICAL OPERATING CHARACTERISTICS (-40°C TO +125°C)

Test Conditions: PVin=Vin=12V, VCC=6.8V, Vout = 1.2V, L=470nH, Switching Frequency = 300kHz, T_A= 25° C and natural convention cooling unless otherwise noted.

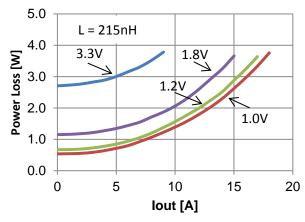
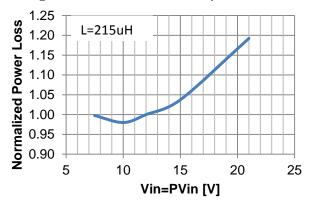


Figure 5: Power Loss vs. Output Current



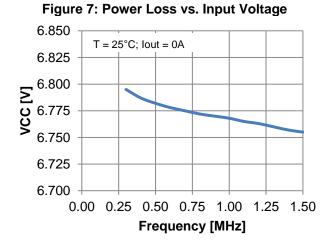


Figure 9: VCC vs. Frequency

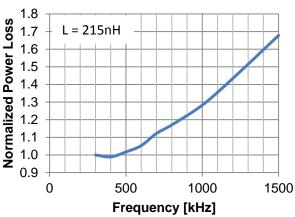


Figure 6: Power Loss vs. Switching Frequency

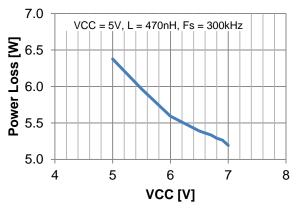
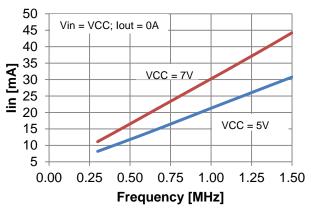


Figure 8: Power Loss vs. Driver Supply Voltage







TYPICAL OPERATING CHARACTERISTICS (-40°C TO +125°C)

Test Conditions: PVin=Vin=12V, VCC=6.8V, Vout = 1.2V, L=470nH, Switching Frequency = 300kHz, T_A= 25° C and natural convention cooling unless otherwise noted.

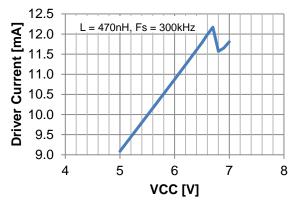
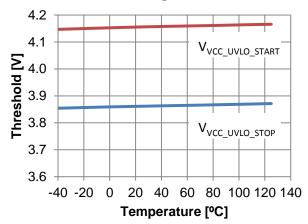


Figure 11: Driver Supply Current vs. Driver Supply Voltage





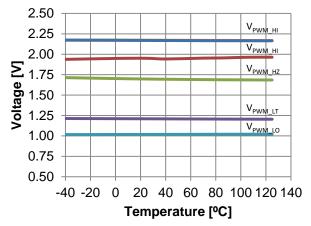
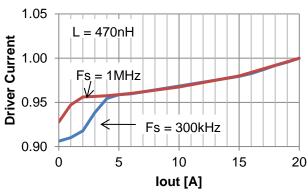
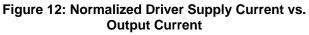
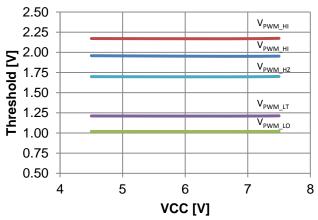
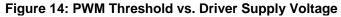


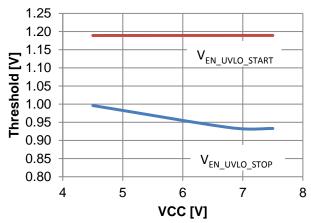
Figure 15: PWM Threshold vs. Temperature













TYPICAL OPERATING CHARACTERISTICS (-40°C TO +125°C)

Test Conditions: PVin=Vin=12V, VCC=6.8V, Vout = 1.2V, L=470nH, Switching Frequency = 300kHz, T_A= $25^{\circ}C$ and natural convention cooling unless otherwise noted.

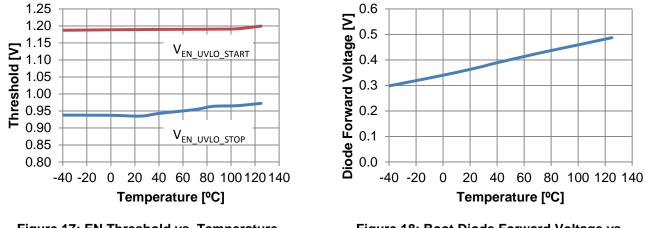
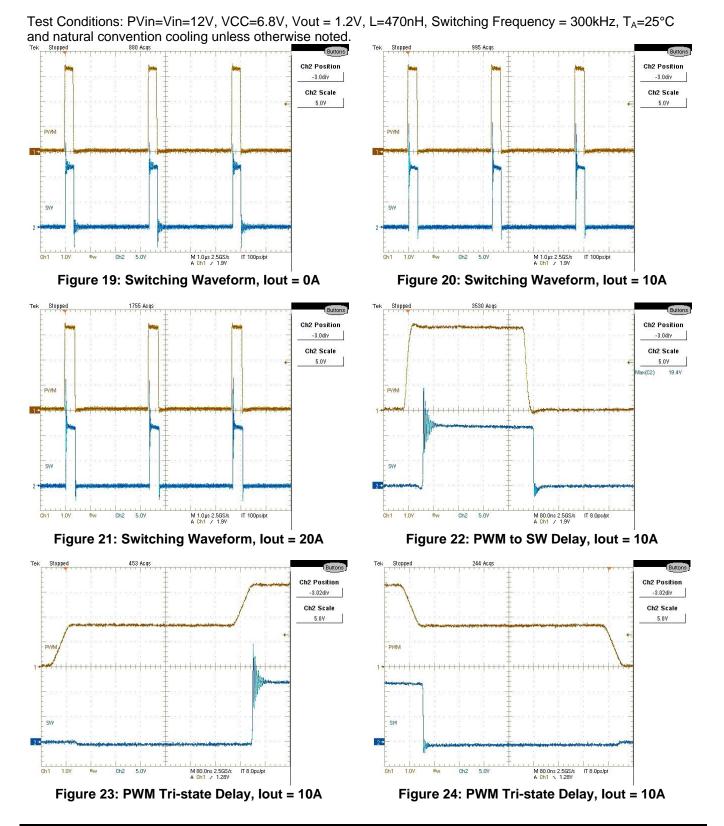


Figure 17: EN Threshold vs. Temperature

Figure 18: Boot Diode Forward Voltage vs. Temperature

TYPICAL OPERATING CHARACTERISTICS (-40°C TO +125°C)



THEORY OF OPERATION

DESCRIPTION

The IR3742 PowIRStage[®] is a synchronous buck driver with co-packed MOSFETs with integrated Schottky diode, which provices system designers with ease of use and flexibility required in medium current low-profile applications.

The IR3742 is designed to work with a PWM controller. The IR3742 PWM input is compatible with 3.3V logic signal and 7V tolerant. It accepts 3-level PWM input signals with tri-state.

The IR3742 provides a fault indicator that monitors over current events and over temperature events.

UNDER-VOLTAGE LOCKOUT AND POR

The Power On Ready (POR) circuit monitors the voltage of V_{CC}/LDO_Output pin and the Enable pin. It assures that the MOSFET driver outputs remain off whenever either of these two signals is below the set thresholds. The POR signal is generated when all these signals reach the valid logic level (see system block diagram). Normal operation resumes once both V_{CC}/LDO_Output and Enable voltages rise above their thresholds.

ENABLE/EXTERNAL PVIN MONITOR

The IR3742 has an Enable function providing another level of flexibility for start-up. The Enable pin has a precise threshold which is internally monitored by Under-Voltage Lockout (UVLO) circuit. If the voltage at Enable pin is below its UVLO threshold, both high-side and low-side FETs are off. When Enable pin is below its UVLO, and Fault stays low.

The Enable pin should not be left floating. A pulldown resistor in the range of several kilo-ohms is recommended to between the Enable Pin and ground.

In addition to being a logical input, the Enable pin can help form a precise input voltage UVLO. As shown in Figure 25, the input of the Enable pin is derived from the PV_{in} voltage by a resistive divider, R1 and R2. By selecting different divider ratios, users can program the UVLO threshold voltage for the bus voltage UVLO. It prevents the IR3742 from regulating at PV_{in} lower than the desired voltage level. Figure 26 shows the start-up waveform with the input UVLO voltage set at 10V.

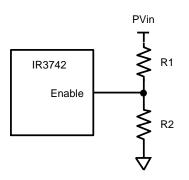
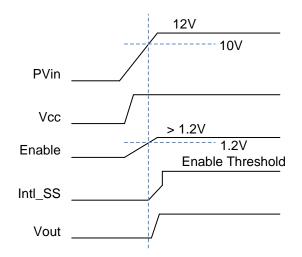
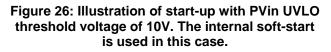


Figure 25: Implementation of Input Under-Voltage Lockout (UVLO) using Enable Pin





INTERNAL LDO

The IR3742 has an internal Low Dropout Regulator (LDO), offering 6.8V. 6.8 $V_{\rm CC}$ voltage results in higher full load efficiency due to less conduction loss.

The internal LDO is beneficial for single rail (supply) applications, where no external bias supplies will be



IR3742

needed. For these applications, V_{in} pin should be connected to PV_{in} and V_{CC}/LDO_Out pin is left floating as shown in Figure 27. 1.0 μ F and 2.2 μ F ceramic bypass capacitors should be placed close to V_{in} pin and V_{CC}/LDO_Out pin respectively.

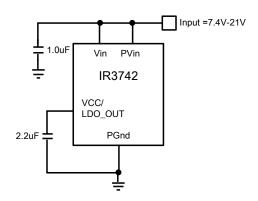


Figure 27: Internally Biased Single-Rail Configuration

 V_{CC}/LDO_Out pin can be directly connected to the PV_{in} pin to bypass the internal LDO and therefore to avoid the voltage drop on the internal LDO. This configuration is illustrated in Figure 28.

Figure 29 shows the configuration using an external V_{CC} voltage. With this configuration, the input voltage range can be extended down to 1.0V.

It should be noted as the V_{CC} voltage decreases, the efficiency and the over current limit will decrease due to the increase of $R_{DS(ON)}$. Please refer to the section of the over current protection for more information.

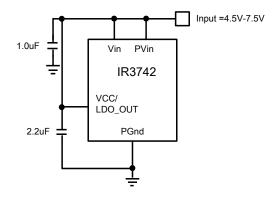


Figure 28: Single-Rail Configuration for 4.5V-7V inputs

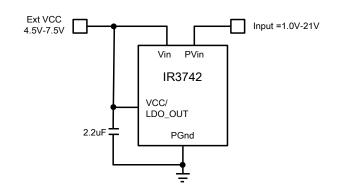


Figure 29: Use External Bias Voltage

PWM TRI-STATE INPUT

The IR3742 PWM accepts 3-level input signals. When PWM input is high, the synchronous MOSFET is turned off and the control MOSFET is turned on. When the PWM input is low, control MOSFET is turned off and synchronous MOSFET is turned on. Figure 19 - Figure 24 show the PWM input and the corresponding SW output of the IR3742. If PWM pin is floated, the built-in resistors pull the PWM pin into a tri-state region centered about 1.65V.

OVER CURRENT INDICATOR AND OC_EN

The over current indication monitors the current through the Synchronous MOSFET using $R_{DS(on)}$ sensing. This method enhances the converter's efficiency and reduces cost by eliminating a current sense resistor and any layout related noise issues. The current limit is pre-set internally and is compensated according to the IC temperature. So at different ambient temperature, the over-current threshold remains almost constant.

Over current is measured at the valley of the inductor current. Over current events are flagged after PWM goes high and the internal LDrv signal goes low. The drivers follow the PWM signal even when an over current event is detected and/or the Fault indicator is set.

OC_en signal enables the over current fault indicator functionality. IR3742 pulls Fault low when an over current event is detected, if OC_en is set high. If a fault is set, toggling OC_en does not reset the Fault signal.

IQR

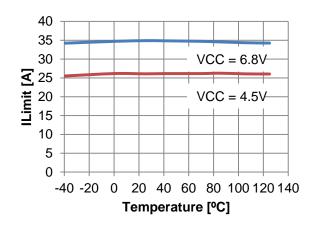


Figure 30: OC Indicator Threshold over temperature

THERMAL FAULT INDICATOR

Temperature sensing is provided inside IR3742. The trip threshold is typically set to 145°C. When trip threshold is exceeded, the open drain fault pin pulls low. The driver will continue switching if a PWM signal is applied and the part is enabled. The fault pin remains low until Enable is pulled low or VCC_UVLO_STOP is triggered.

FAULT OUTPUT

The Fault signal is an open drain signal that requires an external pull up resistor. High state indicates no over current event occurred and no over temperature events were detected. The Fault signal is an indicator that does not prevent the driver from following the PWM signal when set.

Clearing or resetting the Fault signal requires the toggling of the Enable signal or toggling the VCC_UVLO. Fault remains low after setting until it is reset with Enable or VCC.

MINIMUM SWITCH PULSE AND PWM PULSE CONSIDERATIONS

PWM pulses control the switching of the converter in normal operation. However, the IR3742 blanks PWM pulses that are too short. To avoid blanking PWM pulses, ensure the minimum PWM pulse is greater than 70nS. The switch node also has a minimum pulse width. The minimum pulse is the shortest amount of time which Ctrl FET may be reliably turned on.

Any design or application using IR3742 must ensure operation with a pulse width that is longer than this minimum on-time and preferably higher than 70ns. This is necessary for the circuit to operate without jitter and pulse-skipping, which can cause high inductor current ripple and high output voltage ripple.

$$t_{on} = \frac{D}{F_s} = \frac{V_{out}}{V_{in} \times F_s}$$

In any application that uses IR3742, the following condition must be satisfied:

$$t_{on(\min)} \leq t_{on}$$

$$t_{on(\min)} \leq \frac{V_{out}}{V_{in} \times F_s}, \text{ therefore, } V_{in} \times F_s \leq \frac{V_{out}}{t_{on(\min)}}$$

The minimum output voltage is limited by the reference voltage and hence $V_{\text{out}(\text{min})}$ = 0.6 V. Therefore,

$$V_{in} \times F_s \le \frac{V_{out(min)}}{t_{on(min)}} = \frac{0.6V}{70ns} = 8.57V / \mu s$$

Therefore, at the maximum recommended input voltage 21V and minimum output voltage, the converter should be designed at a switching frequency that does not exceed 408 kHz. Conversely, at the maximum switching frequency (1.5 MHz) and minimum output voltage (0.6V), the input voltage (PV_{in}) should not exceed 5.7V, otherwise pulse skipping will happen.

MAXIMUM DUTY RATIO

The maximum duty ratio for the IR3742 is determined by the Toff time. Each cycle requires the gate to be turned off for a minimum of 250nS. This provides an upper limit on the operating duty ratio. IR3742 is designed to operate from 300 kHz to 1.5 MHz. implying maximum duty cycles of 92.5% and 62.5% respectively.



DESIGN EXAMPLE

The following example is a typical application for IR3742. The application circuit is shown in Figure 1.

$$\begin{split} PV_{in} &= V_{in} = 12V \ (\pm 10\%) \\ V_o &= 1.2V \\ I_o &= 20A \\ Peak-to-Peak Ripple Voltage &= \pm 1\% \text{ of } V_o \\ \Delta V_o &= \pm 4\% \text{ of } V_o \ (\text{for } 30\% \text{ Load Transient}) \\ F_s &= 300 \text{ kHz} \end{split}$$

EXTERNAL PVIN MONITOR (INPUT UVLO)

As explained in the section of Enable/External PV_{in} monitor, the input voltage, PV_{in} , can be monitored by connecting the Enable pin to PV_{in} through a set of resistor divider. When PV_{in} exceeds the desired voltage level such that the voltage at the Enable pin exceeds the Enable threshold, 1.2V, the IR3742 is turned on. The implementation of this function is shown in Figure 25.

For a typical Enable threshold of $V_{EN} = 1.2 \text{ V}$

$$PV_{in(\min)} \times \frac{R_2}{R_1 + R_2} = V_{EN} = 1.2$$

$$R_2 = R_1 \times \frac{V_{EN}}{PV_{in(\min)} - V_{EN}}$$

For the minimum input voltage PV_{in (min)} = 9.2V, select R_1 =49.9k Ω , and R_2 =7.5k Ω .

BOOTSTRAP CAPACITOR SELECTION

To drive the Control FET, it is necessary to supply a gate voltage at least 4V greater than the voltage at the SW pin, which is connected to the source of the Control FET. This is achieved by using a bootstrap configuration, which comprises the internal bootstrap diode and an external bootstrap capacitor, C1, as shown in Figure 31. The operation of the circuit is as follows: When the sync FET is turned on, the capacitor node connected to SW is pulled low. V_{CC} starts to charge C1 through the internal bootstrap

diode. The voltage, $V_{c},\ across$ the bootstrap capacitor C1 can be calculated as

$$V_C = V_{CC} - V_D$$

where V_D is the forward voltage drop of the bootstrap diode.

When the control FET turns on in the next cycle, the SW node voltage rises to the bus voltage, PV_{in} . The voltage at the Boot pin becomes:

$$V_{BOOT} = PV_{in} + V_{CC} - V_D$$

A good quality ceramic capacitor of $0.1\mu F$ with voltage rating of at least 25V is recommended for most applications.

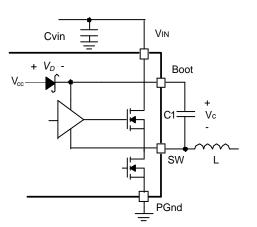


Figure 31: Bootstrap circuit to generate the supply voltage for the high-side driver voltage

INPUT CAPACITOR SELECTION

Good quality input capacitors are necessary to minimize the input ripple voltage and to supply the switch current during the on-time. The input capacitors should be selected based on the RMS value of the input ripple current and requirement of the input ripple voltage.

The RMS value of the input ripple current can be calculated as follows:





$$I_{\rm RMS} = I_o \times \sqrt{D \times (1 - D)}$$

Where D is the duty cycle and I_{o} is the output current. For $I_{o}{=}20A$ and D=0.1, $I_{\text{RMS}}{=}~6A$

The input voltage ripple is the result of the charging of the input capacitors and the voltage induced by ESR and ESL of the input capacitors.

Ceramic capacitors are recommended due to their high ripple current capabilities. They also feature low ESR and ESL at higher frequency which enables better efficiency.

For this application, it is suggested to use three 22μ F/25V ceramic capacitors, C3216X5R1E226M, from TDK. In addition, although not mandatory, a 1x330uF, 25V SMD capacitor EEE-FK1E331P from Panasonic may also be used as a bulk capacitor and is recommended if the input power supply is not located close to the converter.

HIGH OUTPUT VOLTAGE DESIGN CONSIDERATION

When using IR3742 for higher voltage levels, the design should consider maximum duty cycle, power loss and current sensing. Power loss and thermals need to be accounted for when running high loads.

The maximum output voltage is limited by the required off time. When selecting the switching frequency and output voltage, each cycle should never have less than 250nS off time. IR3742 can reach higher output voltages at lower switching frequencies since the required off time is a smaller percentage at slower frequencies.

IR3742 can provide high output voltages, but may require an external cooling. When running high output voltage or higher current rails, care should be taken to ensure the part is adequate cooled.

Inductor current sensing range needs to be addressed. Depending on the controller and current sense methodology, the input range of the current sense circuit maybe a limiting factor on the maximum output voltage.

INDUCTOR SELECTION

The inductor is selected based on output power, operating frequency and efficiency requirements. A low inductor value causes large ripple current, resulting in the smaller size, faster response to a load transient but poor efficiency and high output noise. Generally, the selection of the inductor value can be reduced to the desired maximum ripple current in the inductor (Δ i). The optimum point is usually found between 20% and 40% ripple of the output current.

The saturation current of the inductor is desired to be higher than the over current limit plus the inductor ripple current. An inductor with soft-saturation characteristic is recommended.

For the buck converter, the inductor value for the desired operating ripple current can be determined using the following relation:

$$PV_{in \max} - V_o = L \times \frac{\Delta i_{L \max}}{\Delta t}; \ \Delta t = \frac{D}{F_s}$$
$$L = (PV_{in \max} - V_o) \times \frac{V_o}{V_{in} \times \Delta i_{L \max} \times F_s}$$

Where:

PV_{inmax} = Maximum input voltage

- V_0 = Output Voltage
- Δi_{Lmax} = Maximum Inductor Peak-to-Peak Ripple Current
- F_s = Switching Frequency

 $\Delta t = On time$

D = Duty Cycle

Select $\Delta i_{Lmax} \approx 35\% \times I_o$, then the output inductor is calculated to be 0.51 µH. Select L=0.47 µH, 744309047, from Wurth Electronics which provides an inductor suitable for this application.

OUTPUT CAPACITOR SELECTION

Output capacitors are usually selected to meet two specific requirements: (1) Output ripple voltage and (2) load transient response. The load transient response is also greatly affected by the control bandwidth. So it is common practice to select the output capacitors to meet the requirements of the



output ripple voltage first, and then design the control bandwidth to meet the transient load response. For some cases, even with the highest allowable control bandwidth, the resulting load transient response still cannot meet the requirement. The number of output capacitors then need to be increased.

The voltage ripple is attributed by the ripple current charging the output capacitors, and the voltage drop due to the Equivalent Series Resistance (ESR) and the Equivalent Series Inductance (ESL). Following lists the respective peak-to-peak ripple voltages:

$$\begin{split} \Delta V_{o(C)} &= \frac{\Delta i_{L \max}}{8 \times C_o \times F_s} \\ \Delta V_{o(ESR)} &= \Delta i_{L \max} \times ESR \\ \Delta V_{o(ESL)} &= (\frac{PV_{in} - V_o}{L}) \times ESL \end{split}$$

Where Δi_{Lmax} is maximum inductor peak-to-peak ripple current.

Good quality ceramic capacitors are recommended due to their low ESR, ESL and the small package size. It should be noted that the capacitance of ceramic capacitors are usually de-rated with the DC and AC biased voltage. It is important to use the derated capacitance value for the calculation of output ripple voltage as well as the voltage loop compensation design. The de-rated capacitance value may be obtained from the manufacturer's datasheets.

In this case, three 22uF ceramic capacitors, C2012X5R0J226M, from TDK are used to achieve \pm 12mV peak-to-peak ripple voltage requirement. The de-rated capacitance value with 1.2VDC bias and 10mVAC voltage is around 18uF each.

LAYOUT RECOMMENDATIONS

The layout is very important when designing high frequency switching converters. Layout will affect noise pickup and can cause a good design to perform with worse than expected results.

Make the connections for the power components in the top layer with wide, copper filled areas or polygons. In general, it is desirable to make proper use of power planes and polygons for power distribution and heat dissipation.

The inductor, output capacitors and the IR3742 should be as close to each other as possible. This helps to reduce the EMI radiated by the power traces due to the high switching currents through them. Place the input capacitor directly at the PV_{in} pin of IR3742.

The feedback part of the system should be kept away from the inductor and other noise sources.

The critical bypass components such as capacitors for V_{in} and V_{CC} should be close to their respective pins. In a multilayer PCB use one layer as a power ground plane and have a control circuit ground (analog ground), to which all signals are referenced. The goal is to localize the high current path to a separate loop that does not interfere with the more sensitive analog control function. These two grounds must be connected together on the PC board layout at a single point. It is recommended to place all the compensation parts over the analog ground plane in top layer.

The Power QFN is a thermally enhanced package. Based on thermal performance it is recommended to use at least a 4-layers PCB. To effectively remove heat from the device the exposed pad should be connected to the ground plane using via holes. Figure 32 - Figure 35 illustrates the implementation of the layout guidelines outlined above, on the IRDC3742 4-layer demo board.

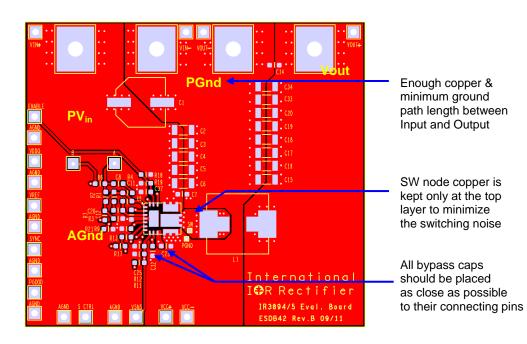
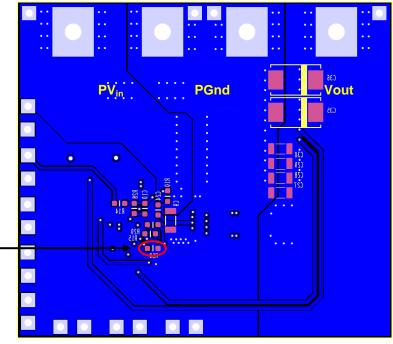


Figure 32: IRDC3742 Demo Board – Top Layer

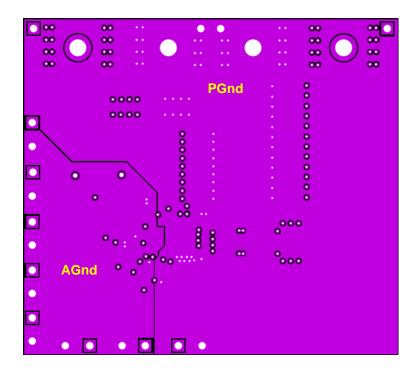






Single point connection between AGND & PGND, should be close to the — PowIRStage kept away from noise sources

Figure 33: IRDC3742 Demo Board – Bottom Layer





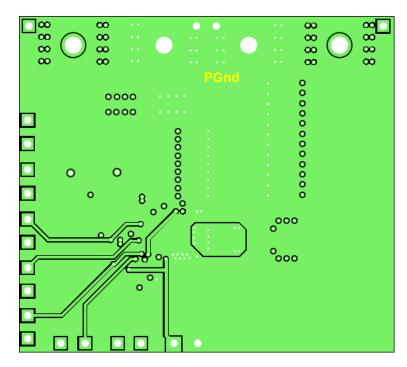


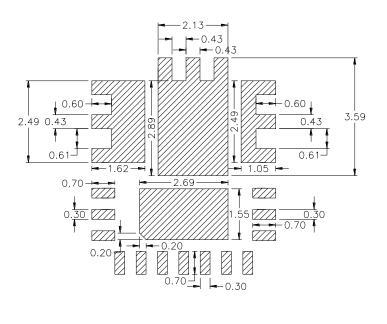
Figure 35: IRDC3742 Demo Board – Middle Layer 2

PCB METAL AND COMPONENT PLACEMENT

Evaluations have shown that the best overall performance is achieved using the substrate/PCB layout as shown in following figures. PQFN devices should be placed to an accuracy of 0.050mm on both X and Y axes. Self-centering behavior is highly dependent on solders and processes, and

experiments should be run to confirm the limits of self-centering on specific processes.

For further information, please refer to "SupIRBuck™ Multi-Chip Module (MCM) Power Quad Flat No-Lead (PQFN) Board Mounting Application Note." (AN1132)



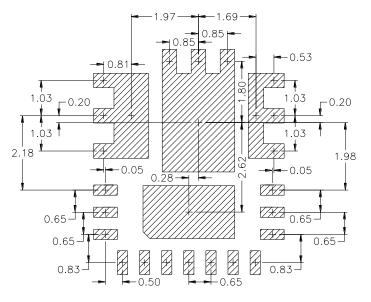


Figure 36: PCB Metal Pad Spacing (all dimensions in mm)

* Contact International Rectifier to receive an electronic PCB Library file in your preferred format



SOLDER RESIST

IR recommends that the larger Power or Land Area pads are Solder Mask Defined (SMD.) This allows the underlying Copper traces to be as large as possible, which helps in terms of current carrying capability and device cooling capability.

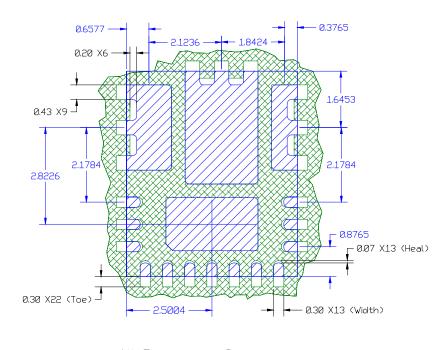
When using SMD pads, the underlying copper traces should be at least 0.05mm larger (on each edge) than the Solder Mask window, in order to accommodate any layer to layer misalignment. (i.e. 0.1mm in X & Y.)

However, for the smaller Signal type leads around the edge of the device, IR recommends that these

are Non Solder Mask Defined (NSMD) or Copper Defined.

When using NSMD pads, the Solder Resist Window should be larger than the Copper Pad by at least 0.025mm on each edge, (i.e. 0.05mm in X&Y,) in order to accommodate any layer to layer misalignment.

Ensure that the solder resist in-between the smaller signal lead areas are at least 0.15mm wide, due to the high x/y aspect ratio of the solder mask strip.



All Dimensions In mm All Pads are Solder Mask Defined Pad Center to Center dimensions



Figure 37: Solder Resist

STENCIL DESIGN

Stencils for PQFN can be used with thicknesses of 0.100-0.250mm (0.004-0.010"). Stencils thinner than 0.100mm are unsuitable because they deposit insufficient solder paste to make good solder joints with the ground pad; high reductions sometimes create similar problems. Stencils in the range of 0.125mm-0.200mm (0.005-0.008"), with suitable reductions, give the best results.

Evaluations have shown that the best overall performance is achieved using the stencil design shown in following figure. This design is for a stencil thickness of 0.127mm (0.005"). The reduction should be adjusted for stencils of other thicknesses.

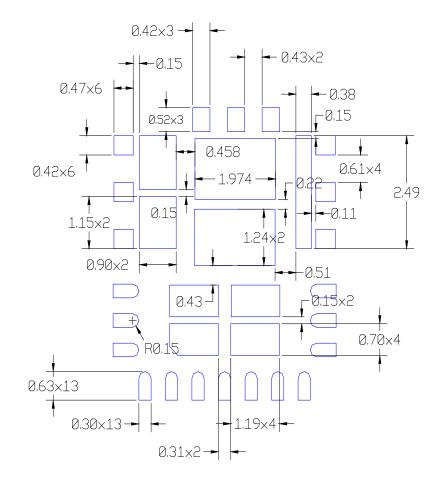
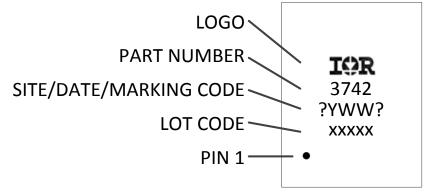


Figure 38: Stencil Pad Spacing (all dimensions in mm)



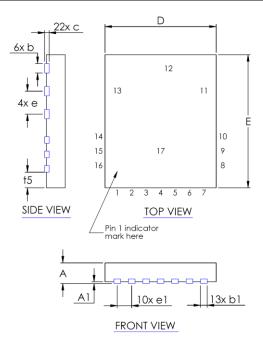
IR3742

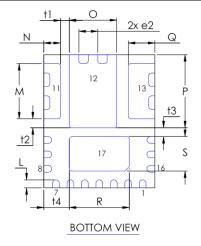
MARKING INFORMATION



PACKAGE INFORMATION

DIM	MILIM	ITERS	INC	HES	DIM	MILIM	ITERS	INC	HES
	MIN	MAX	MIN	MAX	DIN	MIN	MAX	MIN	MAX
Α	0.800	1.000	0.0315	0.0394	L	0.350	0.450	0.0138	0.0177
A1	0.000	0.050	0.0000	0.0020	М	2.441	2.541	0.0961	0.1000
b	0.375	0.475	0.1477	0.1871	Ν	0.703	0.803	0.0277	0.0316
b1	0.250	0.350	0.0098	0.1379	0	2.079	2.179	0.0819	0.0858
С	0.203	REF.	0.008	REF.	Р	3.242	3.342	0.1276	0.1316
D	5.000	BASIC	1.969	BASIC	Q	1.265	1.365	0.0498	0.0537
Е	6.000	BASIC	2.362	BASIC	R	2.644	2.744	0.1041	0.1080
е	1.033	BASIC	0.0407	BASIC	S	1.500	1.600	0.0591	0.0630
e1	0.650	BASIC	0.0256	BASIC	t1, t2, t3	0.401	BASIC	0.016	BACIS
e2	0.852	BASIC	0.0335	BASIC	t4	1.153	BASIC	0.045	BASIC
					t5	0.727	BASIC	0.0286	BASIC





ENVIRONMENTAL QUALIFICATIONS

Qualification Level		Industrial			
Moisture Sensitivity Level		5mm x 6mm PQFN JEDEC Level 2 @ 260°C			
	Machine Model		Class B		
	(JESD22-A115A)	≥200V to <400V			
ESD	Human Body Model	Class 2			
230	(JESD22-A114F)	≥2000V to <4000V			
	Charged Device Model	Class II			
(JESD22-C101D)		≥200V to <500V			
RoHS6 Compliant		Yes			

† Qualification standards can be found at International Rectifier web site: http://www.irf.com

Data and specifications subject to change without notice. Qualification Standards can be found on IR's Web site.

International

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105 TAC Fax: (310) 252-7903 Visit us at www.irf.com for sales contact information. www.irf.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Power Management Specialised - PMIC category:

Click to view products by Infineon manufacturer:

Other Similar products are found below :

LV5686PVC-XH FAN7710VN NCP391FCALT2G SLG7NT4081VTR SLG7NT4192VTR AP4313UKTR-G1 AS3729B-BWLM MB39C831QN-G-EFE2 LV56841PVD-XH AP4306BUKTR-G1 MIC5164YMM PT8A3252WE NCP392CSFCCT1G PT8A3284WE PI3VST01ZEEX PI5USB1458AZAEX PI5USB1468AZAEX MCP16502TAC-E/S8B MCP16502TAE-E/S8B MCP16502TAA-E/S8B MCP16502TAB-E/S8B TCKE712BNL,RF ISL91211AIKZT7AR5874 ISL91211BIKZT7AR5878 MCP16501TC-E/RMB ISL91212AIIZ-TR5770 ISL91212BIIZ-TR5775 CPX200D AX-3005D-3 TP-1303 TP-1305 TP-1603 TP-2305 TP-30102 TP-4503N MIC5167YML-TR LPTM21-1AFTG237C LR745N8-G MPS-3003L-3 MPS-3005D SPD-3606 STLUX383A TP-60052 LM26480SQ-AA/NOPB LM81BIMTX-3/NOPB LM81CIMT-3/NOPB MIC5166YML-TR GPE-4323 GPS-2303 GPS-3303